

#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

Device	BV <sub>DSS</sub>	R <sub>D1</sub> R <sub>D2</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C (Note 10)
N-	30V	$22m\Omega$ @ $V_{GS} = 10V$	17A
Channel	30 V	$28m\Omega @ V_{GS} = 4.5V$	14A

#### **Features and Benefits**

- Ultra Low Gate Threshold Voltage
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Function
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Description**

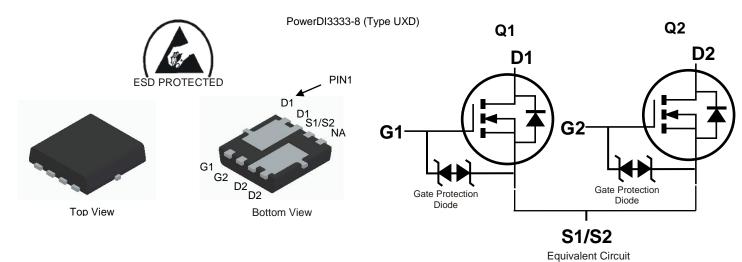
This new generation MOSFET is designed to minimize the on-state resistance (R<sub>D1</sub>R<sub>D2</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### **Applications**

- General Purpose Interfacing Switch
- Power Management Functions

## **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8 (Type UXD)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072 grams (Approximate)



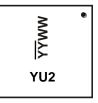
# **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT3022UEV-7	PowerDI3333-8 (Type UXD)	2,000/Tape & Reel
DMT3022UEV-13	PowerDI3333-8 (Type UXD)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



YU2 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 18 for 2018)

WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Q1 & Q2	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	ID	17 14	А	
Maximum Body Diode Forward Current (Note 6)		I <sub>S</sub>	2	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	50	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty C	I <sub>SM</sub>	50	A	
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	19	Α	
Avalanche Energy (Note 7) L = 0.1mH	Eas	18.5	mJ	

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	137	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)  Steady State		$R_{\theta JA}$	70	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>eJC</sub>	12	C/VV	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. UIS in production with L = 0.1mH, starting  $T_A = +25$ °C.

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

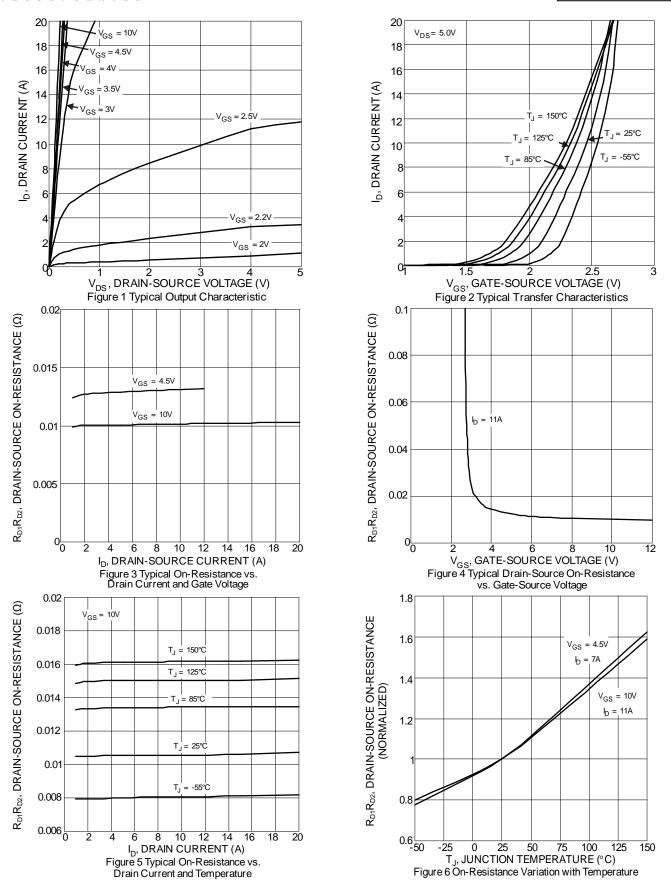
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	12.2	22	mΩ	$V_{GS} = 10V, I_D = 11A$	
Static Dialii-Source Oil-Resistance	$R_{D1}R_{D2}$		17.6	28		$V_{GS} = 4.5V, I_D = 7A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 8.8A$	
DYNAMIC CHARACTERISTICS (Note 9)			_				
Input Capacitance	C <sub>iss</sub>	_	903	_		$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$	
Output Capacitance	Coss	_	386	_	pF		
Reverse Transfer Capacitance	$C_{rss}$	1	67	_			
Gate Resistance	R <sub>G</sub>	_	1.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	13.9	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	6.9	_	nC V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A		
Gate-Source Charge	Q <sub>GS</sub>	_	1.5	_	IIC	$V_{DS} = 15V, I_{D} = 10A$	
Gate-Drain Charge	$Q_{GD}$	_	2.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.8	_			
Turn-On Rise Time	t <sub>R</sub>	_	6.7	_		$V_{GS} = 10V, V_{DD} = 15V, R_G = 1\Omega,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.5	_	ns	$I_D = 8.8A$	
Turn-Off Fall Time	t <sub>F</sub>	_	1.7	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	17	_	ns	1 0 0 0 4:/44 400 0 ///-	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	Q <sub>RR</sub> — 6.8		_	nC	I <sub>F</sub> = 8.8A, di/dt = 100A/μs	

Notes: 8. Short duration pulse test used to minimize self-heating effect.

Guaranteed by design. Not subject to product testing.
 Package limited.

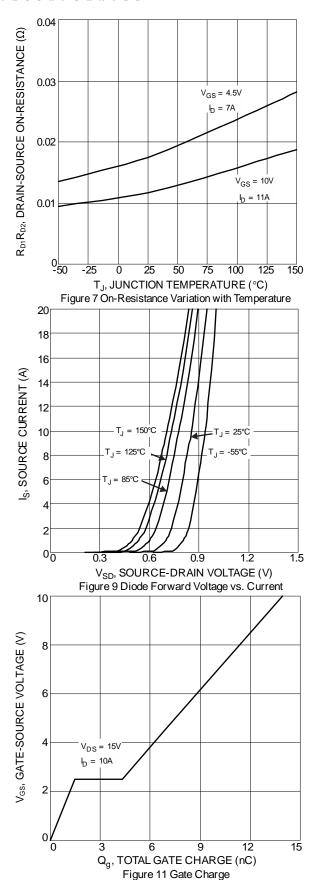


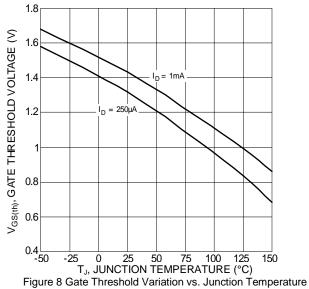


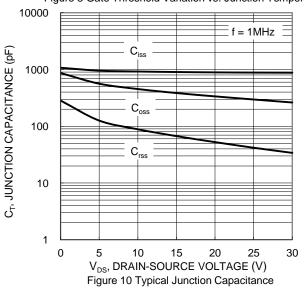


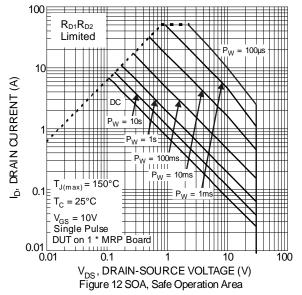




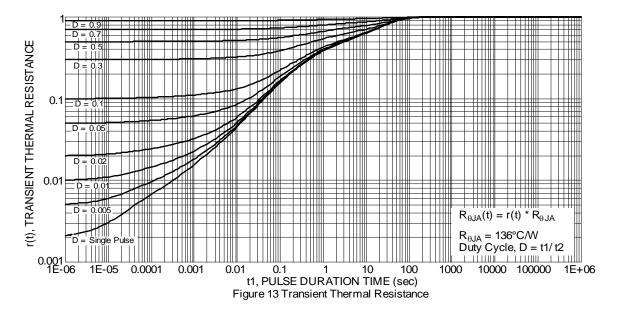










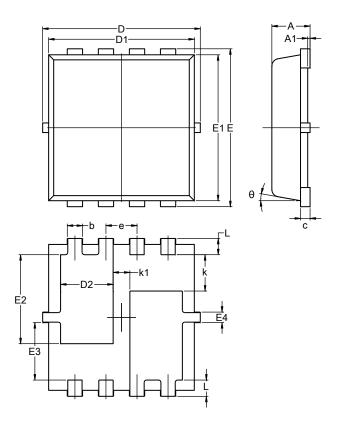




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UXD)

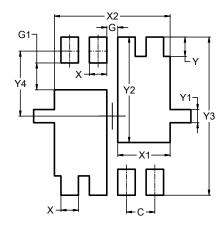


PowerDI3333-8					
(Type UXD)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	0.90	1.30	1.10		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.66	2.06	1.86		
E3	1.10	1.30	1.20		
E4	0.12	0.32	0.22		
е	-	-	0.65		
L	0.24	0.44	0.34		
k	0.56	0.96	0.76		
k1	0.15	0.55	0.35		
θ	0°	12°	10°		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UXD)



Dimensions	value (in mm)			
С	0.650			
G	0.250			
G1	0.610			
Х	0.400			
X1	1.200			
X2	2.650			
Υ	0.440			
Y1	0.300			
Y2	2.400			
Y3	3.600			
Y4	1.480			



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